Low Voltage, Dual SPDT Analog Switch with Charge Pump

DESCRIPTION

The DG2616, DG2617, DG2618 are monolithic CMOS analog switching products designed for high performance switching of analog signals. Combining low power, high speed, low on-resistance and small physical size, the DG2616, DG2617, DG2618 are ideal for portable and battery powered applications.

The DG2616, DG2617, DG2618 have built-in charge-pump circuitry which lowers the minimum supply voltage to + 1.5 V while maintaining low on-resistance. The Control circuitry allows the DG2616, DG2617, DG2618 to operate in different configurations.

Built on Vishay Siliconix's low voltage process, the DG2616, DG2617, DG2618 has an epitaxial layer that prevents latch-up. Break-before-make is guaranteed.

The DG2616, DG2617, DG2618 are manufactured in space saving DFN-10 ($3.0 \times 3.0 \text{ mm}$). And as a committed partner to the community and the environment, Vishay Siliconix manufactures this product with lead (Pb)-free device terminations and is 100 % RoHS compliant.

FEATURES

- Low voltage operation (1.5 V to 3.6 V)
- Low on-resistance R_{ON}: 4.2 Ω typ. at 2.7 V
 - Fast switching: t_{ON} = 39 ns
 - t_{OFF} = 8 ns
- DFN-10 package

BENEFITS

- Reduced power consumption
- High accuracy
- Reduce board space
- TTL/1.8 V logic compatible
- High bandwidth

APPLICATIONS

- Cellular phones
- Audio and video signal routing
- PCMCIA cards
- · Battery operated systems

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION

TRUTH TABLE DG2616					
Logic	NC1, 2	NO1, 2			
0	ON	OFF			
1	OFF	ON			

TRUTH TABLE DG2617							
SHDN/EN Logic	IN Logic	NC1, 2	NO1, 2	Charge Pump			
0	0	ON	OFF	ON			
0	1	OFF	ON	ON			
1	0	ON	OFF	OFF			
1	1	OFF	ON	OFF			

TRUTH TABLE DG2618							
SHDN/EN Logic	IN Logic	NC1, 2	NO1, 2	Charge Pump			
0	0	ON	OFF	ON			
0	1	OFF	ON	ON			
1	х	OFF	OFF	OFF			

ORDERING INFORMATION					
Temp. Range	Package	Part Number			
- 40 °C to 85 °C	DFN-10	DG2616DN-T1-E4 DG2617DN-T1-E4 DG2618DN-T1-E4			



RoHS

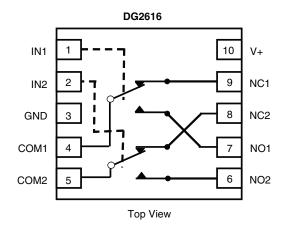
COMPLIANT

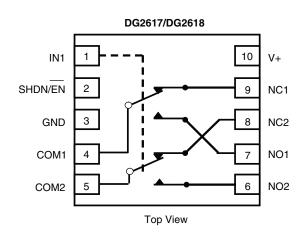


DG2616, DG2617, DG2618

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ABSOLUTE MAXIMUM RATINGS $T_A = 25 ^{\circ}C$, unless otherwise noted					
Parameter		Limit	Unit		
Reference to GND	V+	- 0.3 to 6.0	V		
Reference to GIND	IN, COM, NC, NO ^a	- 0.3 to (V+ + 0.3)	V		
Current (Any terminal except NO, NC or COM)		30			
Continuous Current (NO, NC, or COM)		± 150	mA		
Peak Current (Pulsed at 1 ms, 10 % Duty Cycle)		± 300			
Storage Temperature (D-Suffix)		- 65 to 150			
Package Solder Reflow Conditions ^d			- °C		
Power Dissipation (Packages) ^b	DFN-10 ^c	1191	mW		

Notes:

a. Signals on NC, NO, or COM or IN exceeding V+ will be clamped by internal diodes. Limit forward diode current to maximum current ratings.

b. All leads welded or soldered to PC board.

c. Derate 14.9 mW/°C above 70 $^\circ\text{C}$

d. Manual soldering with iron is not recommended for leadless components. The DFN-10 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper lip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.



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Parameter Symbol $V + = 3 V, \pm 10 %, V_{IN} = 0.5 \text{ or } 1.4 V^{\circ}$ Temp. ⁴ Min. ^b Typ. ^c Max. ^b Analog Switch	Parameter		Test Conditions Otherwise Unless Specified		Limits - 40 °C to 85 °C			
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$		Symbol	-	Temp. ^a		1	1 .	Uni
	Analog Switch	-						
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	Analog Signal Range ^d			Full	0		V+	V
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $			V+ = 1.5 V, V _{COM} = 1.5 V, I _{NO} , I _{NC} = 10 mA			5.3		
$ \begin{array}{ c c c c c c c } \hline \begin{tabular}{ c c c c c } \hline \begin{tabular}{ c c c c c c c } \hline \begin{tabular}{ c c c c c c c c c c c c c c c c c c c$				Room			7.0	
$\begin{tabular}{ c c c c c c } \hline $V_{+} = 3.6 & V_{V_{COM}} = 3.6 & V_{I_{NO}, I_{NO}} = 10 & mA & $Poom_{Full}$ & P_{OII} & $S.5$ & 7.0 & 8.0 \\ \hline P_{OII} & P_{Iull} & $V_{+} = 3.6 & V_{V_{COM}} = 1.5 & V_{2.7} & $V_{I_{NO}, I_{NC}} = 10 & mA & $Poom_{Full}$ & 0.6 & 2.0 \\ \hline P_{OI} & AP_{ON} & $V_{+} = 3.6 & V_{V_{COM}} = 1.7 & V_{I_{NO}, I_{NC}} = 10 & mA & $Poom_{Full}$ & 0.6 & 2.0 \\ \hline P_{OII} & $V_{+} = 3.6 & V_{V_{COM}} = 1.7 & V_{I_{NO}, I_{NC}} = 10 & mA & $Poom_{Full}$ & 1.5 & 2.7 & V_{Iul} & $V_{+} = 3.6 & V_{V_{OO}} & $V_{10C} = 1.0 & M_{10} & V_{11} & V	On-Resistance	RON	$V = 2.7 V, V_{COM} = 2.7 V, I_{NO}, I_{NC} = 10 MA$	Full		4.7	8.0	
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $			V+ = 3.6 V, V _{COM} = 3.6 V, I _{NO} , I _{NC} = 10 mA	Room		5.5	7.0	Ω
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$	R _{ON} Flatness ^d	_	V+ = 2.7 V, V _{COM} = 1.5 V, 2.7 V,			0.6		
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	R _{ON} Match ^d		I_{NO} , I_{NC} = 10 mA	Room		0.1		
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	On Resistance (Shutdown)	R _{SHDN}	V+ = 3.6 V, V _{COM} = 1.7 V, I _{NO} , I _{NC} = 10 mA			15	-	
		I _{NO(off)} ,			- 2			nA
$\begin{array}{c c c c c c c c c c c c c c c c c c c $	Switch Off Leakage Current	I _{NC(off)}		Full			10	
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	0	I _{COM(off)}	V _{COM} = 3.3 V/0.3 V					
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	-	I _{COM(on)}	V+ = 3.6 V, V _{NO} , V _{NC} = V _{COM} = 0.3 V/3.3 V	Room	- 2		2	
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $		I					-	
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	Input High Voltage	Vinili			1.0			
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$	input ngir tonago			Full	1.4			v
$\begin{array}{c c c c c c c c c c c c c c c c c c c $	Input Low Voltage	V _{INL}		_				ł
$\begin{array}{c c c c c c c c c c c c c c c c c c c $	Input Capacitance	C _{in}		Full		3.2	0.0	pF
Dynamic CharacteristicsTurn-On Time t_{ON} t_{OFF} $V_{+} = 2.7 \text{ or } 3.6 \text{ V}, V_{NO} \text{ or } V_{NC} = 1.5 \text{ V},$ $R_{L} = 50 \Omega, C_{L} = 35 \text{ pF}$ $\begin{array}{c c c c c c c c c } Room & 39 & 69 & 76 & 76 & 76 & 76 & 76 & 76 & 7$			V _{IN} = 0 or V+	Full	- 1		1	μA
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	Dynamic Characteristics					•		
Turn-Off Time t_{OFF} $V_{+} = 2.7 \text{ or } 3.6 \text{ V}, V_{NO} \text{ or } V_{NC} = 1.5 \text{ V},$ $R_{L} = 50 \Omega, C_{L} = 35 \text{ pF}$ R_{OOM} 939Break-Before-Make Time t_{d} $R_{L} = 50 \Omega, C_{L} = 35 \text{ pF}$ $Room$ 939Charge Injection ^d Q_{INJ} $C_{L} = 1 \text{ nF}, V_{GEN} = 0 \text{ V}, R_{GEN} = 0 \Omega$ $Room$ 7Off-Isolation ^d $OIRR$ $R_{L} = 50 \Omega, C_{L} = 5 \text{ pF}, f = 1 \text{ MHz}$ $Room$ 7Off-Isolation ^d $OIRR$ $R_{L} = 50 \Omega, C_{L} = 5 \text{ pF}, f = 100 \text{ MHz}$ $Room$ -77 $Crosstalk^{d, f}$ X_{TALK} $R_{L} = 50 \Omega, C_{L} = 5 \text{ pF}, f = 100 \text{ MHz}$ $Room$ -32No No Off Capacitance ^d $C_{NO(off)}$ $R_{L} = 50 \Omega, C_{L} = 5 \text{ pF}, f = 100 \text{ MHz}$ $Room$ 9	Turn-On Time	t _{ON}				39		
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $			V+ = 2.7 or 3.6 V, V _{NO} or V _{NC} = 1.5 V,			0		
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	Turn-Off Time	t _{OFF}	$R_L = 50 \Omega$, $C_L = 35 pF$			9		ns
$\begin{array}{c c} R_L = 50 \ \Omega, \ C_L = 5 \ pF, \ f = 1 \ MHz \\ \hline OIRR & R_L = 50 \ \Omega, \ C_L = 5 \ pF, \ f = 100 \ MHz \\ \hline R_L = 50 \ \Omega, \ C_L = 5 \ pF, \ f = 100 \ MHz \\ \hline Crosstalk^{d, \ f} & X_{TALK} & R_L = 50 \ \Omega, \ C_L = 5 \ pF, \ f = 100 \ MHz \\ \hline R_L = 50 \ R_L =$	Break-Before-Make Time	t _d		Full	1			
$\begin{array}{c c c c c c c c c c c c c c c c c c c $	Charge Injection ^d	Q _{INJ}		Room		7		pC
$\begin{array}{c c c c c c c c c c c c c c c c c c c $	orre en d	0155				- 77		- dB
$\begin{array}{c c c c c c c c c c c c c c c c c c c $	Ott-Isolation ⁴	OIKK		Room		- 32		
No. No. Off Capacitance ^d C _{NO(off)} Room 9	Crosstalk ^{d, f}	XTALK		-				
No No Off Canacitance ^a	UIUSSIAIK 7		$H_L = 50 \Omega$, $C_L = 5 pF$, $f = 100 MHz$	Desire				
	N _O , N _C Off Capacitance ^d							
f = 1 MHz		C _{NC(off)}	f = 1 MHz	Room				pF
Channel-On Capacitance ^d C _{NO(on)} Room 21 Room 19	Channel-On Capacitance ^d		+					-



SPECIFICATIONS $V + = 3 V$								
		Test Conditions Otherwise Unless Specified		Limits - 40 °C to 85 °C				
Parameter	Symbol	V+ = 3 V, \pm 10 %, V $_{\rm IN}$ = 0.5 or 1.4 V $^{\rm e}$	Temp. ^a	Min. ^b	Typ. ^c	Max. ^b	Unit	
Power Supply								
Power Supply Range	V+			1.5		3.6	V	
Power Supply Current	l+	V + = 3.6 V, V_{IN} = 0 or V+, SHDN/ \overline{EN} = 0 V	Full		104	300	uА	
	1+	V + = 3.6 V, V_{IN} = 0 or V+, SHDN/ \overline{EN} = V+			0.1	2	μΑ	

Notes:

a. Room = 25 $^{\circ}$ C, Full = as determined by the operating suffix.

b. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.

c. Typical values are for design aid only, not guaranteed nor subject to production testing.

d. Guarantee by design, not subjected to production test.

e. V_{IN} = input voltage to perform proper function.

f. Crosstalk measured between channels.

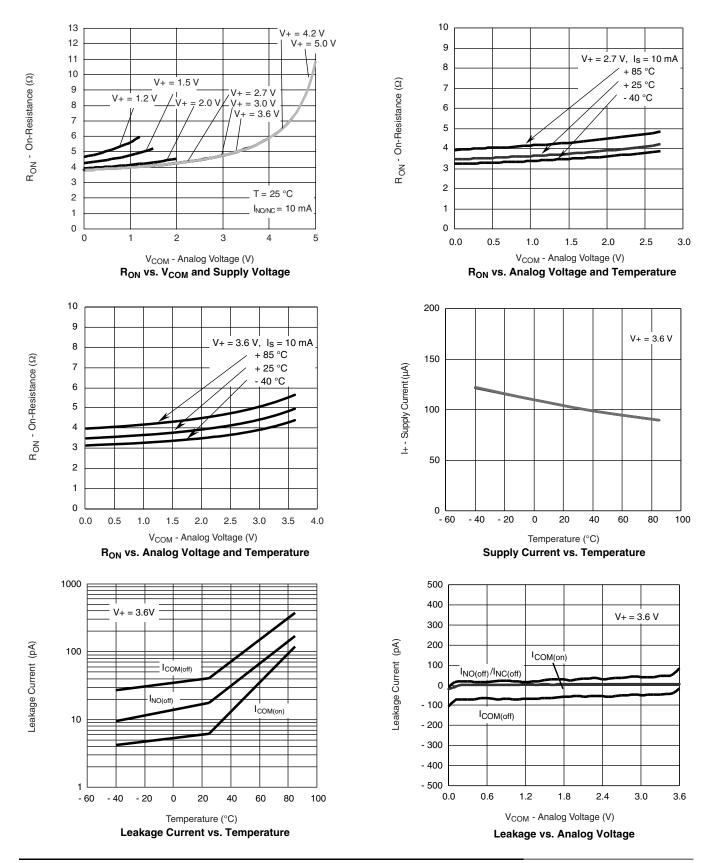
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



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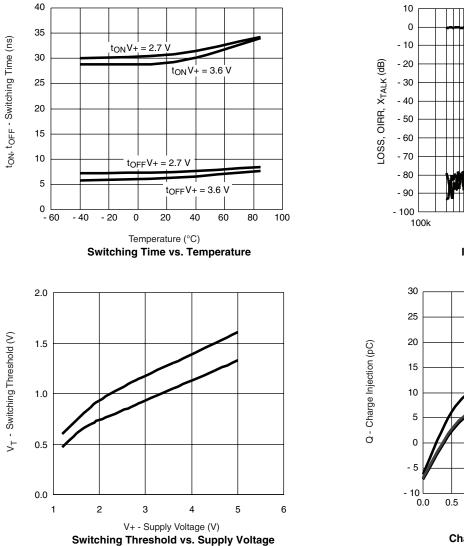
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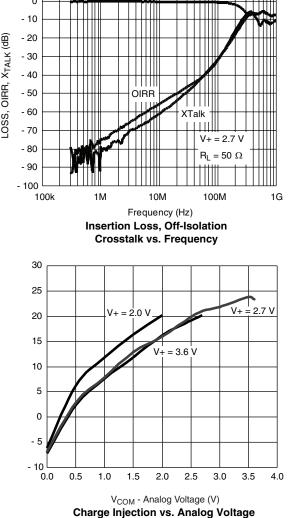
TYPICAL CHARACTERISTICS $T_A = 25$ °C, unless otherwise noted



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TYPICAL CHARACTERISTICS $T_A = 25$ °C, unless otherwise noted





Loss

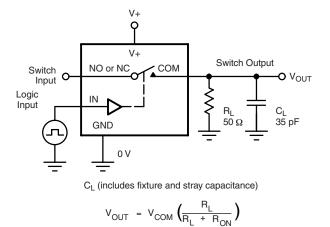
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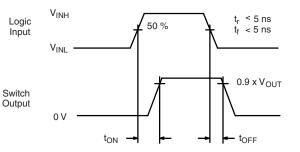


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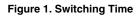
Vishay Siliconix

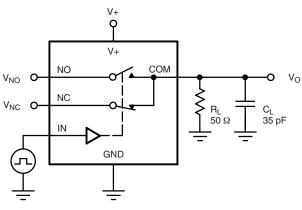
TEST CIRCUITS

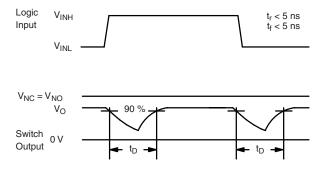




Logic "1" = Switch On Logic input waveforms inverted for switches that have the opposite logic sense.

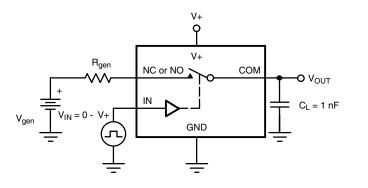


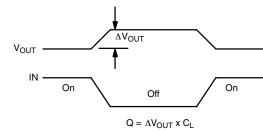




C_L (includes fixture and stray capacitance)

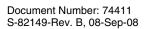
Figure 2. Break-Before-Make Interval



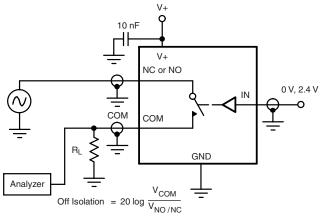


IN depends on switch configuration: input polarity determined by sense of switch.

Figure 3. Charge Injection



TEST CIRCUITS



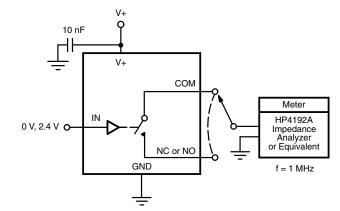


Figure 4. Off-Isolation

Figure 5. Channel Off/On Capacitance

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